

Figure 1. DRCLS of ZnGeN<sub>2</sub> grown on GaN (top right) and c-Sapphire (bottom right) showing a high degree of uniformity in depth with deconvolutions of the 0.5kV spectra (left) revealing the differences between ZnGeN<sub>2</sub> grown on GaN vs Al<sub>2</sub>O<sub>3</sub>.

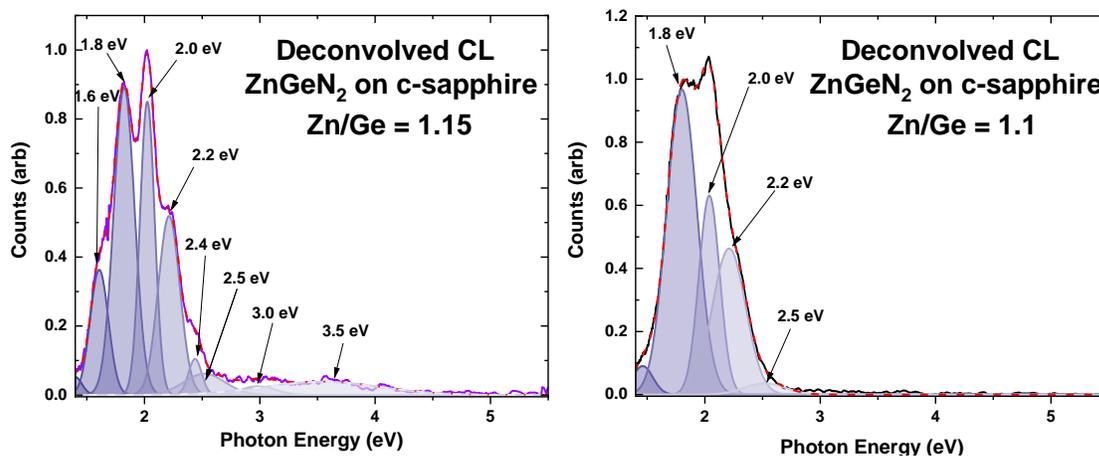


Figure 2. Cathodoluminescence of ZnGeN<sub>2</sub> at 0.5kV comparing films with Zn/Ge = 1.15 (left) and Zn/Ge = 1.1 (right).

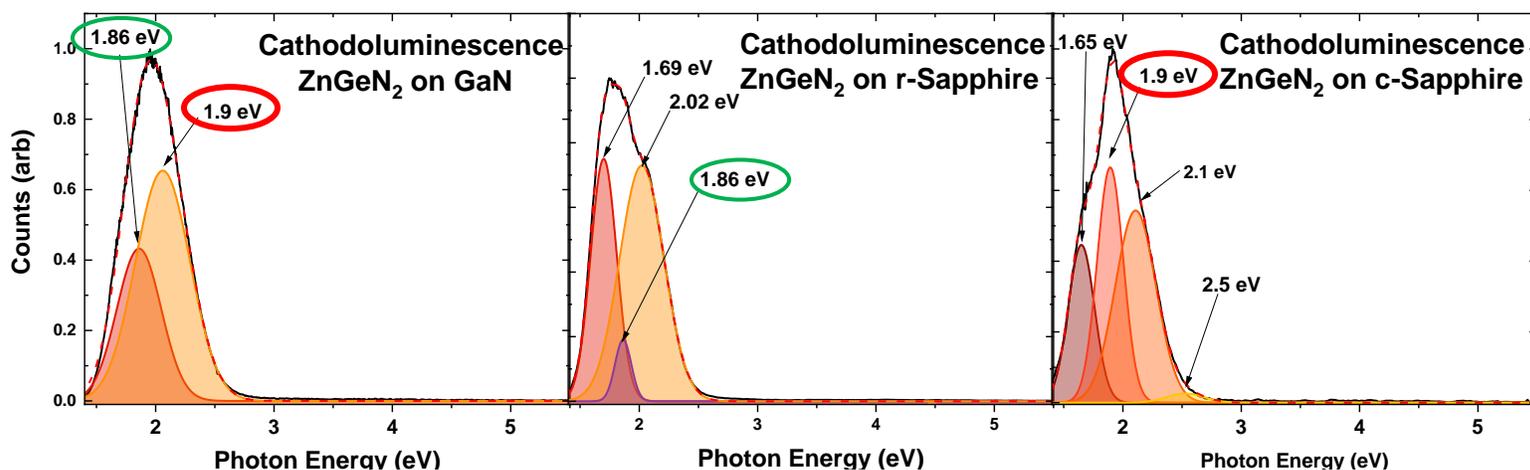


Figure 3. Comparison of ZnGeN<sub>2</sub> grown on GaN (left), r-sapphire (middle), and c-sapphire (right). The dominant peaks of ZnGeN<sub>2</sub> on GaN also appear in films grown on c-sapphire (red ovals) and on r-sapphire (green ovals).